

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
27 January 2005 (27.01.2005)

PCT

(10) International Publication Number
WO 2005/008892 A1

(51) International Patent Classification⁷: **H03K 19/00**, 17/06

(21) International Application Number:
PCT/US2004/021529

(22) International Filing Date: 1 July 2004 (01.07.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/617,897 10 July 2003 (10.07.2003) US

(71) Applicant (for all designated States except US): **QUALCOMM INCORPORATED** [US/US]; 5775 Morehouse Drive, San Diego, California 92121 (US).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **FAHIM, Amr** [CA/US]; 871 Stevens Avenue, #1301, Solana Beach, California 92075 (US).

(74) Agents: **PATEL, Milan** et al.; 5775 Morehouse Drive, San Diego, CA 92121 (US).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

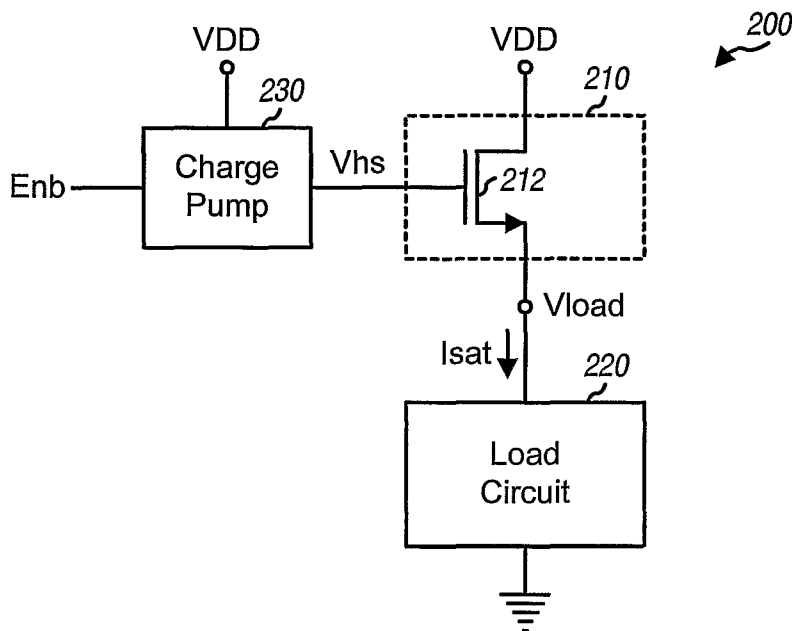
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA,

[Continued on next page]

(54) Title: LOW-POWER N-FET HIGH-SIDE SWITCH



(57) Abstract: An N-FET high-sideswitch (210) has improved performance (e.g., less leakage current, lower ON resistance, and smaller area) over a conventional P-FET high-sideswitch. The N-FET high-sideswitch (210) includes at least one N-FET device (212) and couples between a power supply (VDD) and a load circuit (220), which may be, e.g., a microprocessor, a digital signal processor, or a memory unit. The high-sideswitch (210) couples the power supply (VDD) to the load circuit (220) when the high-sideswitch (210) is enabled and cuts off the power supply (VDD) from the load circuit (220) when disabled. A charge pump (230) couples to the high-sideswitch (210) and provides a control signal (Vhs). This control signal (Vhs) is sufficiently high when the high-sideswitch (210) is enabled to ensure that the N-FET device (212) operates in a linear region and has

a small drain to source voltage drop. The high-sideswitch (210) may be operated as a power switch or in a feedback configuration to implement a linear or a digital voltage regulator.

WO 2005/008892 A1



MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii)) for all designations

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.